

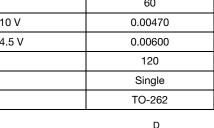
www.vishay.com

Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.00470				
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.00600				
I _D (A)	120				
Configuration	Single				
Package	TO-262				

TO-262



FEATURES

- TrenchFET® power MOSFET
- · Package with low thermal resistance
- AEC-Q101 qualified ^d
- 100 % R_a and UIS tested
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

300

80

320

250

83

-55 to +175



FREE

UNIT

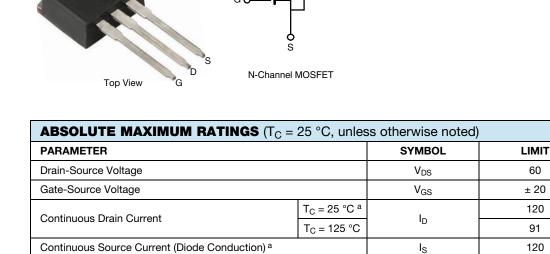
٧

Α

mJ

W

°C



TUPPMAL DECICTANCE DATINGS					
THERMAL RESISTANCE RATINGS PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient F	PCB Mount c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R_{thJC}	0.6	- C/VV	

L = 0.1 mH

 $T_C = 25$ °C

T_C = 125 °C

 I_{DM}

 I_{AS}

E_{AS}

 P_D

 $T_J,\,T_{stg}$

Notes

a. Package limited.

Pulsed Drain Current b

Single Pulse Avalanche Current

Single Pulse Avalanche Energy

Maximum Power Dissipation b

b. Pulse test; pulse width $\leq 300 \, \mu s$, duty cycle $\leq 2 \, \%$.

Operating Junction and Storage Temperature Range

- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		1				l	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$		1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	500	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	120	-	-	Α
		V _{GS} = 10 V	I _D = 30 A	-	0.00378	0.00470	Ω
Drain Source On State Begintance	D	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.00801	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.00992	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.00481	0.00600	
Forward Transconductance b	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	118	-	S
Dynamic ^b							
Input Capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	6705	8800	pF
Output Capacitance	Coss	$V_{GS} = 0 V$		-	904	1200	
Reverse Transfer Capacitance	C _{rss}			-	555	800	
Total Gate Charge ^c	Qg			-	148	230	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_D = 85 \text{ A}$	-	21.4	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	33.2	-	
Gate Resistance	Rg	f = 1 MHz		0.45	0.99	1.5	Ω
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD}=30$ V, $R_L=0.353$ Ω $I_D\cong85$ A, $V_{GEN}=10$ V, $R_g=1$ Ω		-	16	25	
Rise Time ^c	t _r			-	9	15	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	46	75	
Fall Time ^c	t _f			-	12	20	
Source-Drain Diode Ratings and Char	racteristics b						
Pulsed Current ^a	I _{SM}			-	-	300	Α
Forward Voltage	V_{SD}	I _F = 70 A, V _{GS} = 0		_	0.92	1.5	V

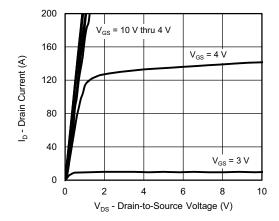
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

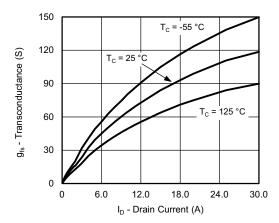
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



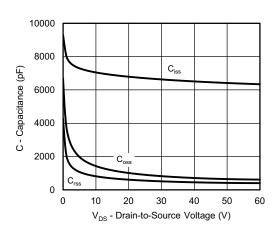
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



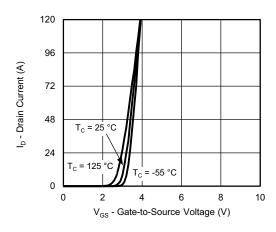
Output Characteristics



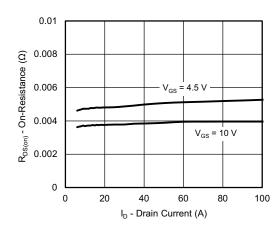
Transconductance



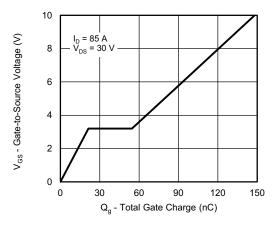
Capacitance



Transfer Characteristics



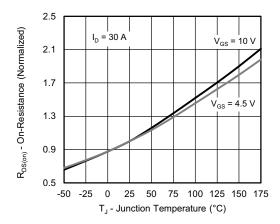
On-Resistance vs. Drain Current



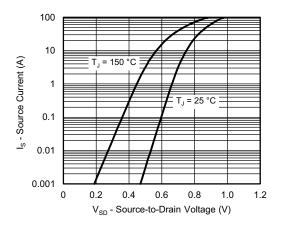
Gate Charge



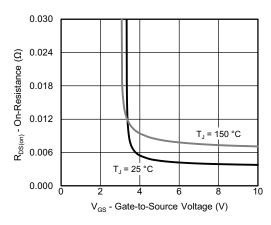
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



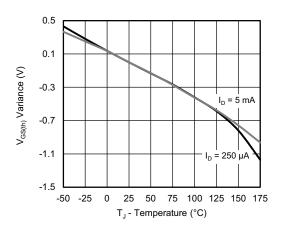
On-Resistance vs. Junction Temperature



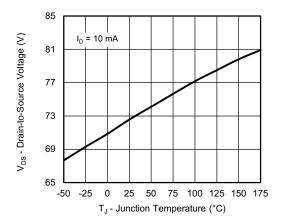
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



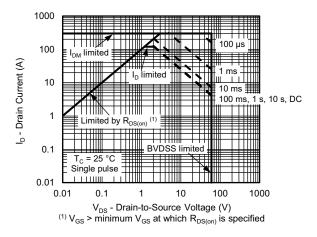
Threshold Voltage



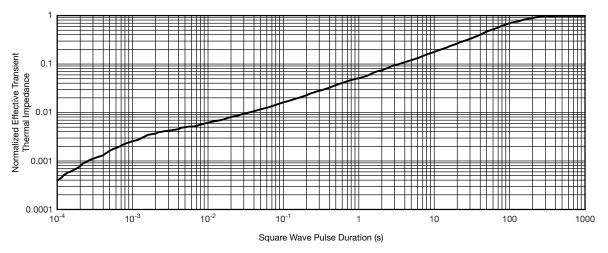
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



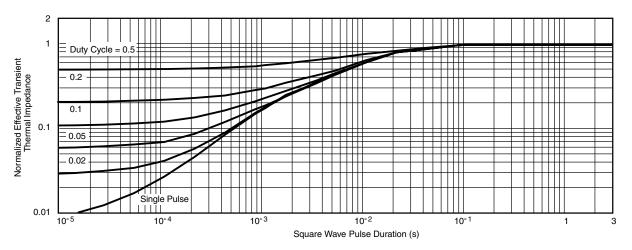
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

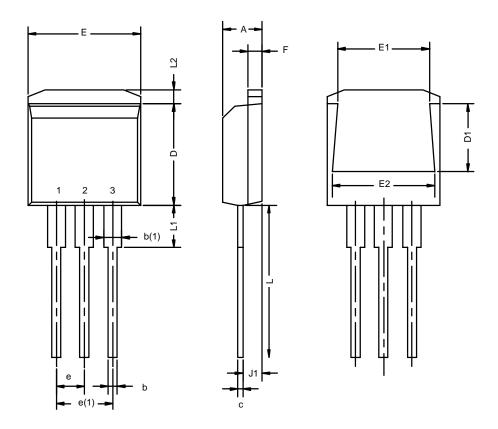
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg266962.



TO-262: **3-LEAD**



	MILLIM	ETERS*	INC	INCHES		
Dim	Min	Max	Min	Max		
Α	4.32	4.70	0.170	0.185		
b	0.64	1.00	0.025	0.039		
b(1)	1.14	1.40	0.045	0.055		
С	0.36	0.50	0.014	0.020		
D	8.64	9.65	0.340	0.380		
D1	5.59	6.10	0.220	0.240		
е	2.41	2.67	0.095	0.105		
e(1)	4.95	5.33	0.195	0.210		
E	10.03	10.41	0.395	0.410		
E1	7.87	8.64	0.310	0.340		
E2	9.02	9.53	0.355	0.375		
F	1.14	1.40	0.045	0.055		
J1	2.41	2.79	0.095	0.110		
L	13.08	14.22	0.515	0.560		
L1	-	3.81	-	0.150		
L2	1.02	1.40	0.040	0.055		
ECN: T-02234—Rev. C, 14-Oct-02 DWG: 5855						

*Use millimeters as the primary measurement

www.vishay.com 15-Oct-02



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